2018 Fall

"Phase Transformation in Materials"

11.13.2018

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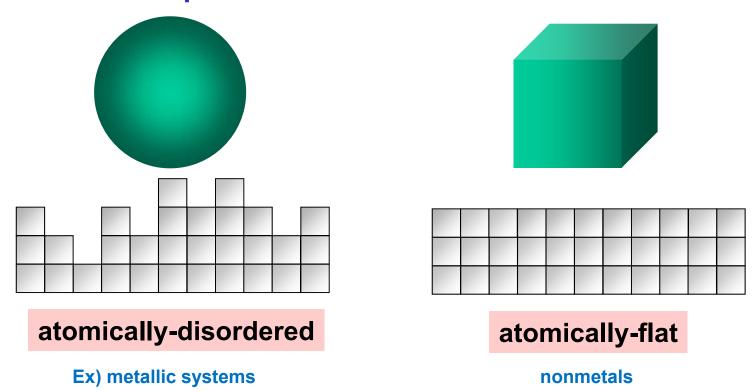
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* Growth

Equilibrium Shape and Interface Structure on an Atomic Scale



Apply thermodynamics to this fact and derive more information.

Entropy-dominant

weak bonding energy

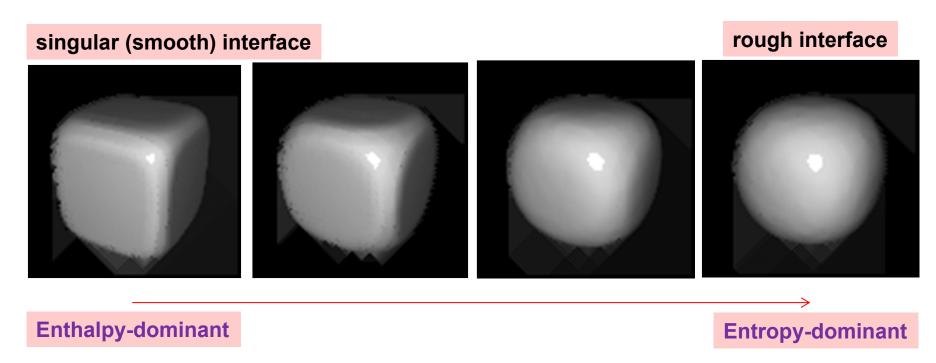
stable at high T

Enthalpy-dominant

strong bonding energy

stable at low T

Thermal Roughening



Heating up to the roughening transition.

Kinetic Roughening

Rough interface - Ideal Growth ightarrow diffusion-controlled ightarrow dendritic growth

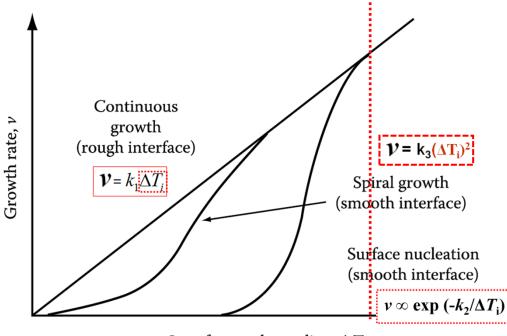
Smooth interface - Growth by Screw Dislocation Growth by 2-D Nucleation

Small $\Delta T \rightarrow$ "feather" type of growth \longleftarrow Large $\Delta T \rightarrow$ cellular/dendritic growth

The growth rate of the singular interface cannot be higher than ideal growth rate.

When the growth rate of the singular Interface is high enough, it follows the ideal growth rate like a rough interface.

→ kinetic roughening

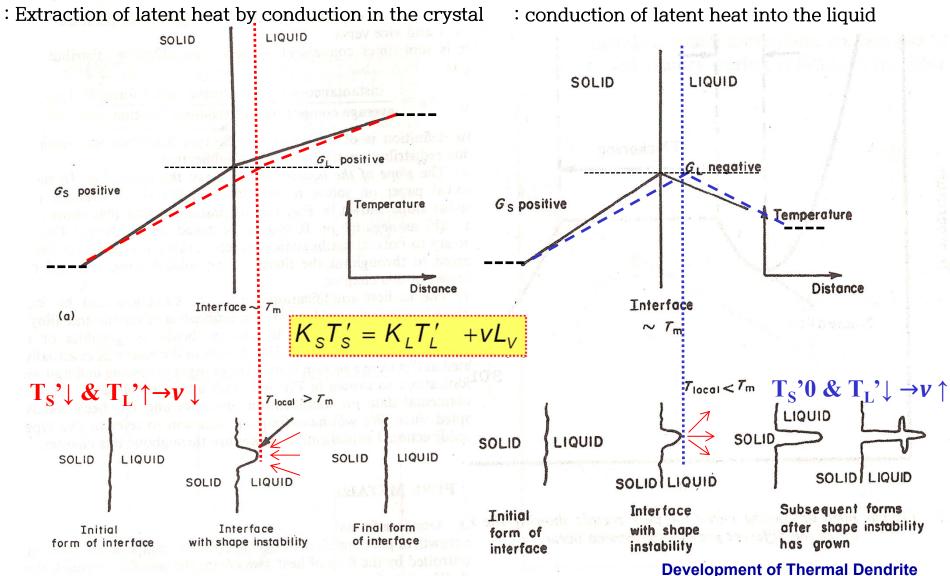


Interface undercooling, ΔT_i

"Removal of latent heat" → Heat Flow and Interface Stability

1) Superheated liquid

2) Supercooled liquid



Closer look at the tip of a growing dendrite

different from a planar interface because heat can be conducted away from the tip in three dimensions.

Assume the solid is isothermal $(T'_{S} = 0)$

From

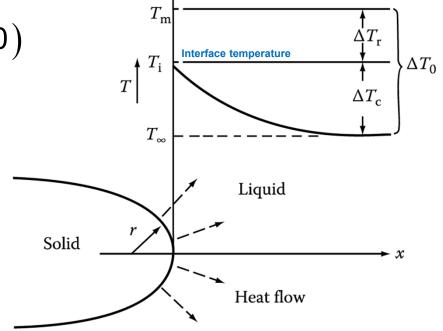
$$K_{S}T_{S}' = K_{L}T_{L}' + vL_{V}$$

If
$$T_{S}' = 0$$
, $V = \frac{-K_{L}T_{L}'}{L_{V}}$

A solution to the heat-flow equation for a hemispherical tip:

$$T_{L}'(negative) \cong \frac{\Delta T_{C}}{r} \quad \Delta T_{C} = T_{i} - T_{\infty}$$

$$v = \frac{-K_{L}T_{L}'}{L_{V}} \cong \frac{K_{L}}{L_{V}} \cdot \frac{\Delta T_{C}}{r} \qquad v \propto \frac{1}{r}$$



However, ΔT also depends on r. How?

Thermodynamics at the tip?

Gibbs-Thomson effect: melting point depression

$$\Delta G = \frac{L_V}{T_m} \Delta T_r = \frac{2\gamma}{r} \qquad \Delta T_r = \frac{2\gamma T_m}{L_V r}$$

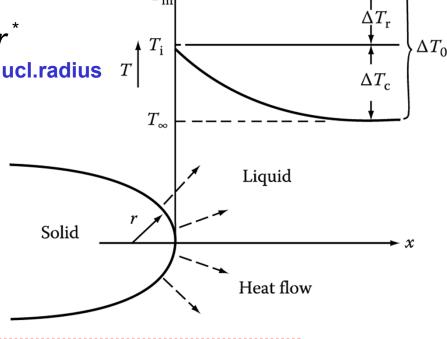
Minimum possible radius (r)?

$$r_{min}: \Delta T_r \to \Delta T_o = T_m - T_\infty \to r^*$$
The crit.nucl.radius
$$r^* = \frac{2\gamma T_m}{L_v \Delta T_o}$$

$$\Delta T_r = \frac{2\gamma T_m}{L_v r}$$

Express ΔT_r by r, r^* and ΔT_o .

$$\Delta T_r = \frac{r^{\hat{}}}{r} \Delta T_o$$



$$V \cong \frac{K_L}{L_V} \cdot \frac{\Delta T_c}{r} = \frac{K_L}{L_V} \cdot \frac{\left(\Delta T_0 - \Delta T_r\right)}{r} = \frac{K_L}{L_V} \cdot \frac{\Delta T_0}{r} \left(1 - \frac{r^*}{r}\right)$$

 $v \to 0$ as $r \to r^*$ due to Gibbs-Thomson effect as $r \to \infty$ due to slower heat condution

Maximum velocity?

$$\rightarrow r = 2r^*$$

Contents for today's class

Solidification: Liquid ---- Solid

< Nucleation > & < Growth >

Nucleation in Pure Metals

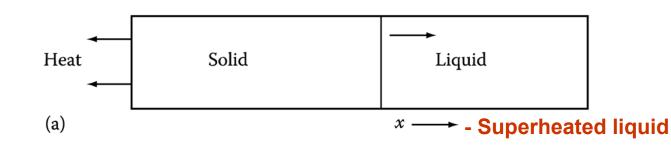
- Equilibrium Shape and Interface Structure on an Atomic Scale
- Growth of a pure solid
- Heat Flow and Interface Stability

4.3 Alloy solidification

- Solidification of single-phase alloys
- Eutectic solidification
- Off-eutectic alloys
- Peritectic solidification

Q: Alloy solidification?

- 1. Solidification of single-phase alloys
- Three limiting cases
 - 1) Equilibrium Solidification: perfect mixing in solid and liquid
 - 2) No Diffusion in Solid, Perfect Mixing in Liquid
 - 3) No Diffusion on Solid, Diffusional Mixing in the Liquid
 - Planar S/L interface → unidirectional solidification



l- Cellular and Dendritic Solidification

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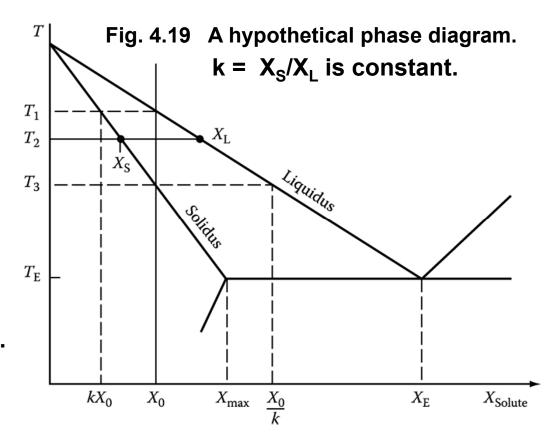
1. Solidification of single-phase alloys

$$k = \frac{X_{S}}{X_{I}} < 1$$

k: partition coefficient

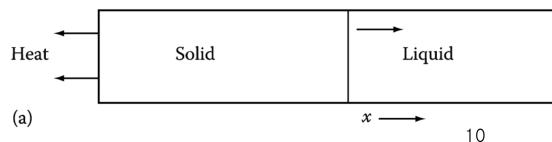
X: mole fraction of solute

In this phase diagram of straight solidus and liquidus, k is const. (independent of T).



Planar S/L interface

→ unidirectional solidification

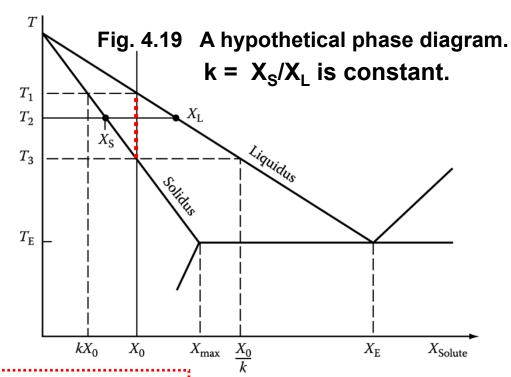


1. Solidification of single-phase alloys

- Three limiting cases
 - 1) Equilibrium Solidification (perfect mixing in solid & liquid)
 - 2) No Diffusion in Solid, Perfect Mixing in Liquid
 - 3) No Diffusion on Solid, Diffusional Mixing in the Liquid
- 1) Equilibrium Solidification (perfect mixing in solid & liquid)
 - → low cooling rate: infinitely slow solidification

$$k = \frac{X_{S}}{1}$$

partition coefficient



- Sufficient time for diffusion in solid & liquid
- Relative amount of solid and liquid: lever rule
- Solidification starts at T_1 ($X_s = kX_0$) and ends at T_3 ($X_L = X_0/k$).

Composition vs x at T_2

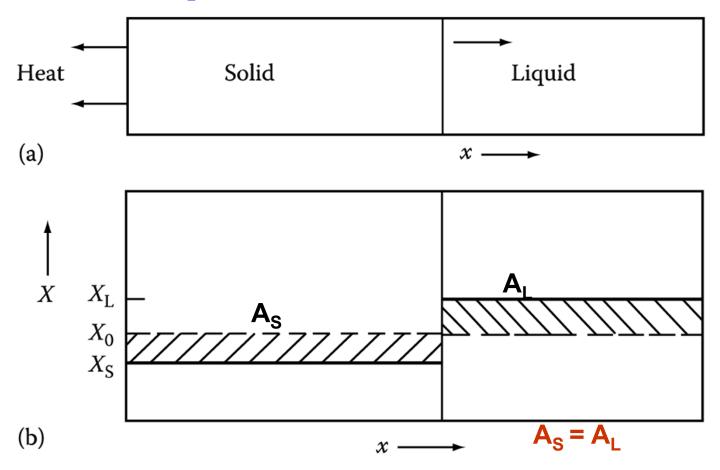
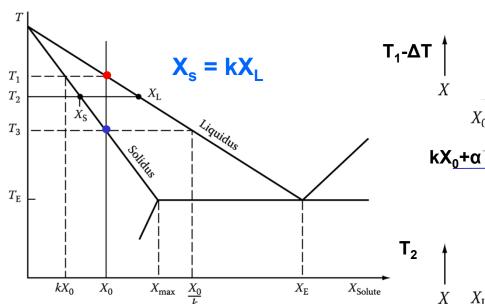


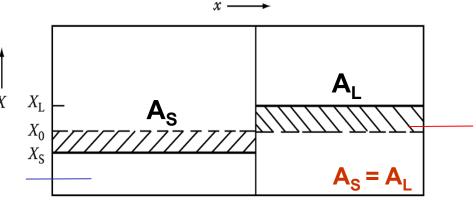
Fig. 4.20 Unidirectional solidification of alloy X_0 in Fig. 4.19. (a) A planar S/L interface and axial heat flow. (b) Corresponding composition profile at T_2 assuming complete equilibrium. Conservation of solute requires the two shaded areas to be equal. $A_s = A_L$

1) Equilibrium Solidification: perfect mixing in solid and liquid

 X_0



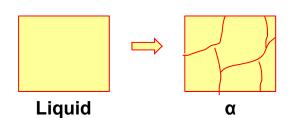
Conservation of solute requires the two shaded areas to be equal.

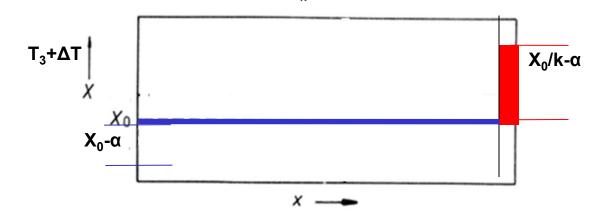


 $X_0+\alpha$

* Equilibrium solute concentration

$$kX_0 \le X_s \le X_0$$
$$X_0 \le X_L \le X_0/k < X_E$$





2) Non-equilibrium Solidification: No Diffusion in Solid, Perfect Mixing in Liquid

: high cooling rate, efficient stirring

- Separate layers of solid retain their original compositions mean comp. of the solid ($\overline{X_s}$) < X_s
- Liquid become richer than $X_0/K \rightarrow X_E$ at the last part of solidification.
- Variation of X_s: solute rejected to the liquid → solute increase in the liquid

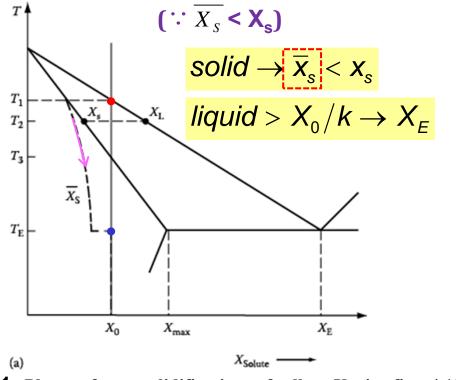
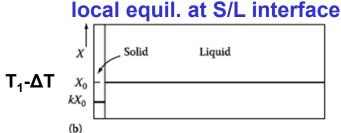
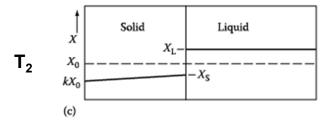
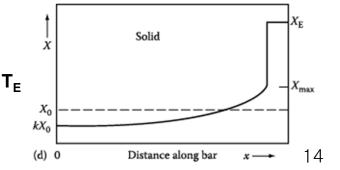


Fig. 4.21 Planar front solidification of alloy X_0 in fig. 4.19 Te assuming no diffusion in the solid, but complete mixing in the liquid. (a) As Fig. 4.19, but including the mean composition of the solid. (b) Composition profile just under T_1 . (c) Composition profile at T_2 (compare with the profile and fraction solidified in Fig.4.20b) (d) Composition profile at the eutectic temperature and below.



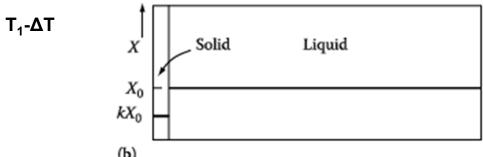


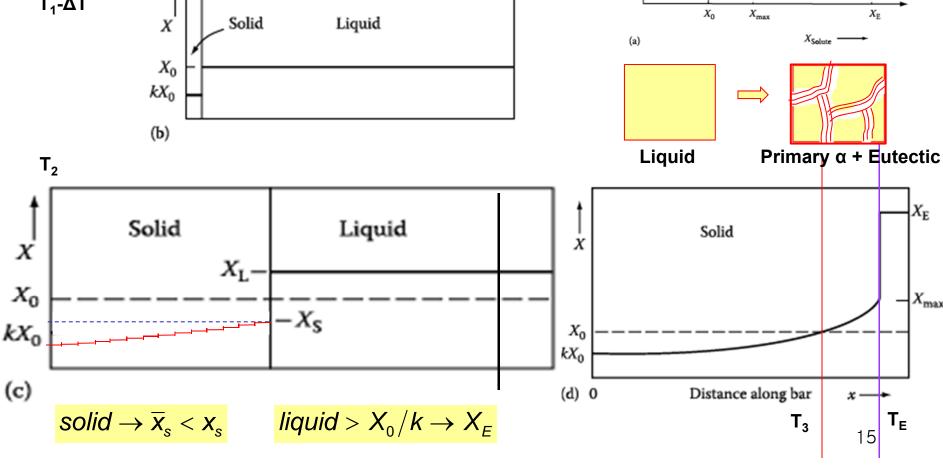


2) No Diffusion in Solid, Perfect Mixing in Liquid

: high cooling rate, efficient stirring

- Separate layers of solid retain their original compositions
- mean comp. of the solid $(\overline{X_s}) < X_s$





L

 $X_{\rm E}$

 $X_{\rm E}$

 $-X_{\text{max}}$

TE

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 T_2

 \overline{x}_{s}

Mass balance: non-equilibrium lever rule (coring structure)

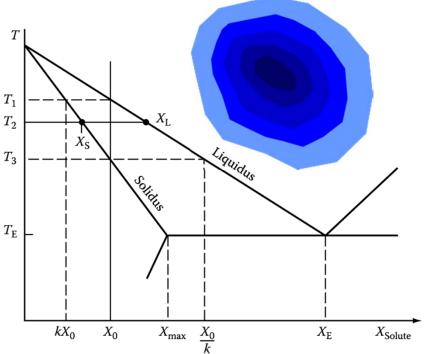
When cooled by ΔT from any arbitrary T, determine the followings.

: solute ejected into the liquid = ?

→ solute increase in the liquid

Ignore the difference in molar volume T_E between the solid and liquid.

f_s: volume fraction solidified



The variation of X_s along the solidified bar

solute ejected into the liquid=? → proportional to what?

 $df_s (X_L - X_S)$

solute increase in the liquid=? → proportional to what?

 $(1-f_s)$ dX_{i}

$$(X_L - X_S)df_S = (1 - f_S)dX_L$$

Solve this equation.

when
$$f_S = 0 \rightarrow X_S$$
, X_L ?

$$X_S = kX_0$$
 and $X_1 = X_0$

$$\int_{0}^{f_{S}} \frac{df_{S}}{1 - f_{S}} = \int_{X_{0}}^{X_{L}} \frac{dX_{L}}{X_{L} - X_{S}} = \int_{X_{0}}^{X_{L}} \frac{dX_{L}}{X_{L} - kX_{L}} = \int_{X_{0}}^{X_{L}} \frac{dX_{L}}{X_{L} (1 - k)}$$

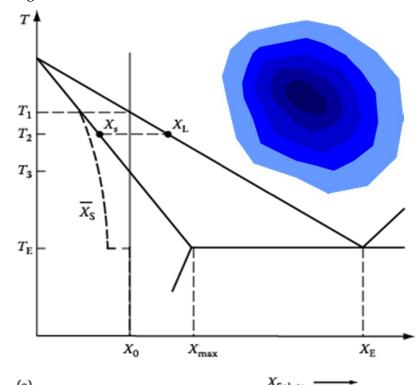
$$\int_0^{f_S} (1-k)(-1)d \ln(1-f_S) = \int_{X_O}^{X_L} d \ln X_L$$

$$\ln \frac{X_L}{X_O} = (k-1)\ln(1-f_S)$$

$$X_{L} = X_{O} f_{L}^{(k-1)}$$

$$X_{S} = kX_{O} (1 - f_{S})^{(k-1)}$$

: non-equilibrium lever rule (Scheil equation)



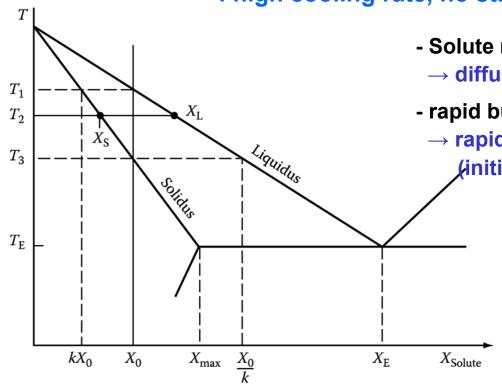
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→ quite generally applicable even for nonplanar solid/liquid interfaces provided here, the liquid composition is uniform and that the Gibbs-Thomson effect is negligible.

"If k<1: predicts that if no diff. in solid, some eutectic always exist to solidify." $(X_s < X_L)$

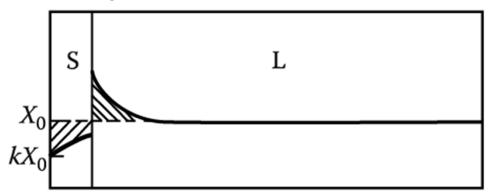
3) No Diffusion on Solid, Diffusional Mixing in the Liquid

: high cooling rate, no stirring→ diffusion



- Solute rejected from solid
 - → diffuse into liquid with limitation
- rapid build up solute in front of the solid
 - → rapid increase in the comp. of solid forming (initial transient)
 - if it solidifies at a const. rate, v, then a steady state is finally obtained at T_3
 - liquid : X₀/k, solid: X₀

local equil. at S/L interface

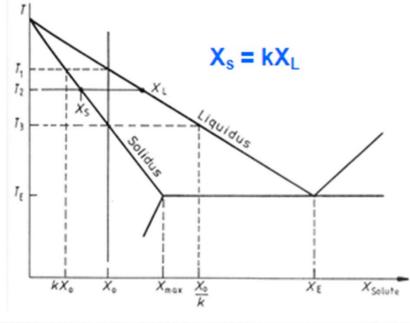


Composition profile at $T_2 < T_{S/L} < T_3$?

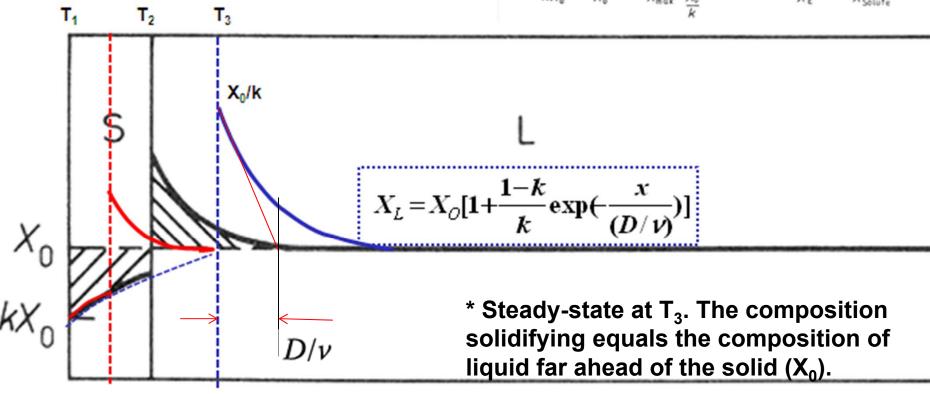
Steady-state profile at T_3 ? at T_E or below?

"Alloy solidification"

- Solidification of single-phase alloys
- No Diffusion on Solid,
 Diffusional Mixing in the Liquid



Interface temperature



No Diffusion on Solid, Diffusional Mixing in the Liquid

During steady-state growth,

(Interface → liquid: Diffusion rate)

Rate at which solute diffuses down the concentration gradient away from the interface = Rate at which solute is rejected from the solidifying liquid

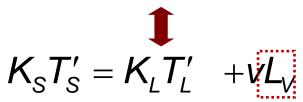
(Solid→Interface: solute rejecting rate)

Set up the equation.

$$J = DC_L' = v(C_L - C_S)$$

$$J = -D\frac{\partial X_L}{\partial X} = v(X_L - X_S)$$

(Solidification rate of alloy: excess solute control)



(Solidification rate of pure metal: latent heat control, 10⁴ times faster than that of alloy)

Solve this equation.

$$X_S = X_0$$
 for all $x \ge 0$

$$\frac{dX_L}{X_L - X_0} = -\frac{v}{D}dx$$

$$\ln(X_L - X_0) = -\frac{v}{D}x + c$$

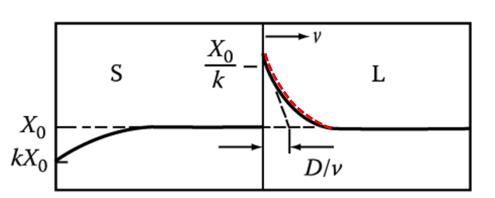
$$x = 0; X_L = X_0 / k$$
steady-state

$$x = 0; X_L = X_0 / k$$

$$c = \ln(\frac{X_0}{k} - X_0)$$

$$\ln \frac{X_L - X_0}{X_0(\frac{1}{k} - 1)} = -\frac{v}{D} x$$

$$X_L - X_0 = X_0 (\frac{1-k}{k}) e^{-\frac{vx}{D}}$$



$$X_L = X_O [1 + \frac{1-k}{k} \exp(-\frac{x}{(D/\nu)})]$$

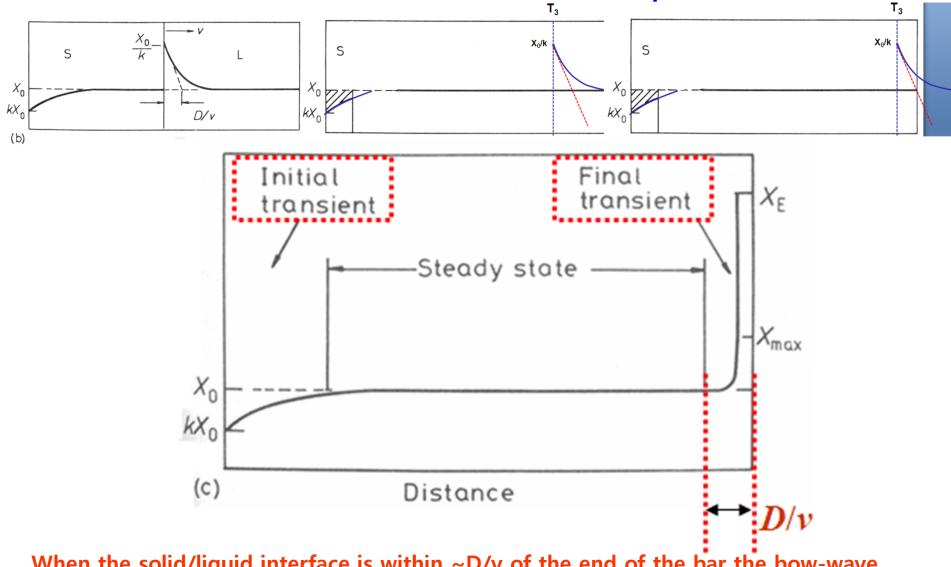
($X_{\underline{l}}$ decreases exponentially from $X_{\underline{0}}/k$ at x=0, the interface, to $X_{\underline{0}}$ at large distances from the interface. The concentration profile has a characteristic width of D/v.)

- The concentration gradient in liquid in contact with the solid :

$$J = -DX'_{L} = v(X_{L} - X_{S}) \qquad X'_{L} = -\frac{X_{L} - X_{S}}{D/v}$$

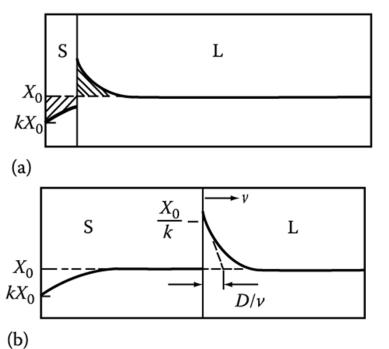
"Alloy solidification" - Solidification of single-phase alloys

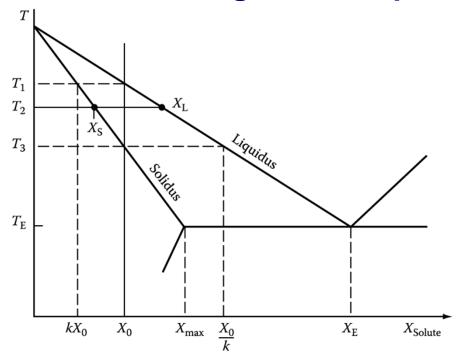
* No Diffusion on Solid, Diffusional Mixing in the Liquid



When the solid/liquid interface is within ~D/v of the end of the bar the bow-wave of solute is compressed into a very small volume and the interface composition rises rapidly leading to a final transient and eutectic formation.

No Diffusion on Solid, Diffusional Mixing in the Liquid





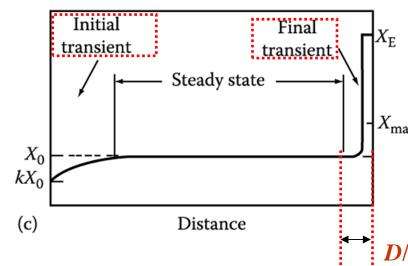
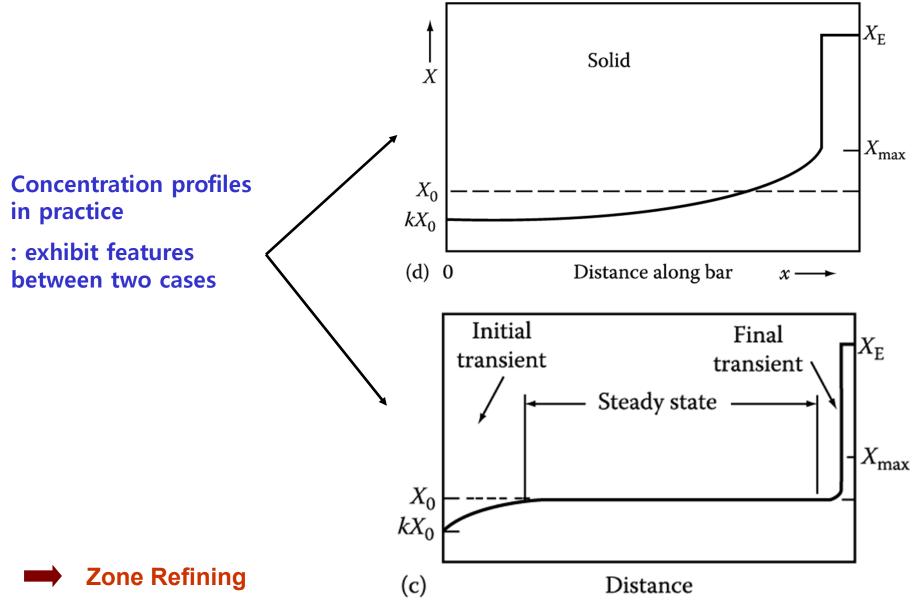


Fig. 4.22 Planar front solidification of alloy X_0 in Fig. 4.19 assuming no diffusion in solid and no stirring in the liquid.

- (a) Composition profile when S/L temperature is between T_2 and T_3 in Fig. 4.19.
- $X_{\rm ma}$ (b) Steady-state at T $_3$. The composition solidifying equals the composition of liquid far ahead of the solid (X $_0$).
 - (c) Composition profile at T_E and below, showing the final transient.

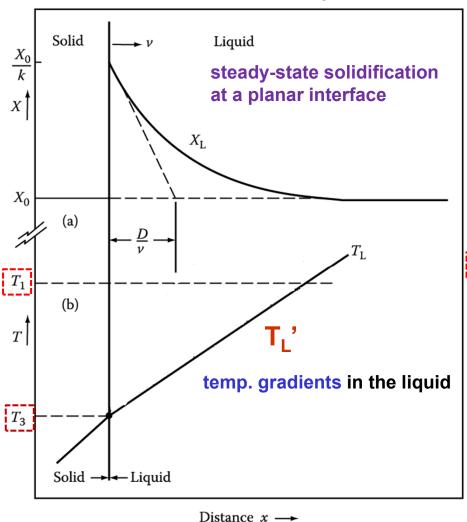


Q: Cellular and Dendritic Solidification by "constitutional supercooling" in alloy

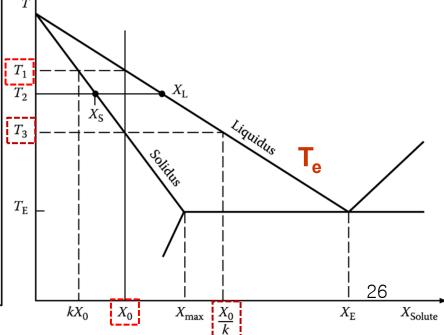
2. Cellular and Dendritic Solidification

Fast Solute diffusion similar to the conduction of latent heat in pure metal, possible to break up the planar front into dendrites.

→ complicated, however, by the possibility of temp. gradients in the liquid.

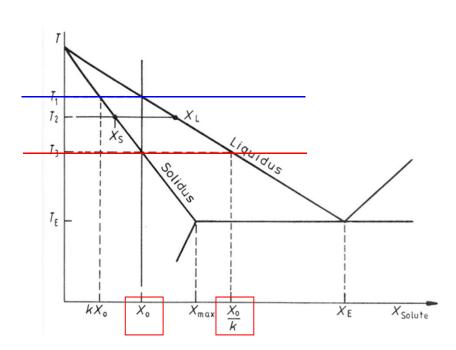


What would be T_e along the concentration profile ahead of the growth front during steady-state solidification?



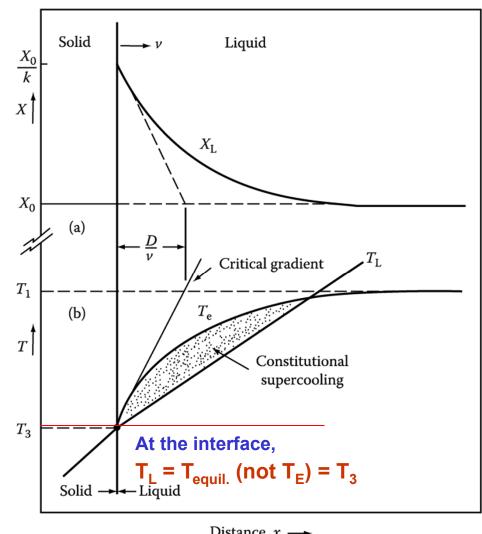
* Constitutional Supercooling

No Diffusion on Solid, Steady State **Diffusional Mixing in the Liquid**



* Actual temperature gradient in Liquid

* equilibrium solidification temp. change



Distance $x \longrightarrow$

: the protrusion melts back - Planar interface: stable $T_L' > (T_1 - T_3)/(D/v)$

 $T_{L}'/v < (T_{1}-T_{3})/D$

Q: Planer → Cell structure → Dendrite?

by constitutional supercooling in superheated liquid

If temperature gradient ahead of an initially planar interface is gradually reduced below the critical value, (constitutional supercooling at solid/liquid interface)

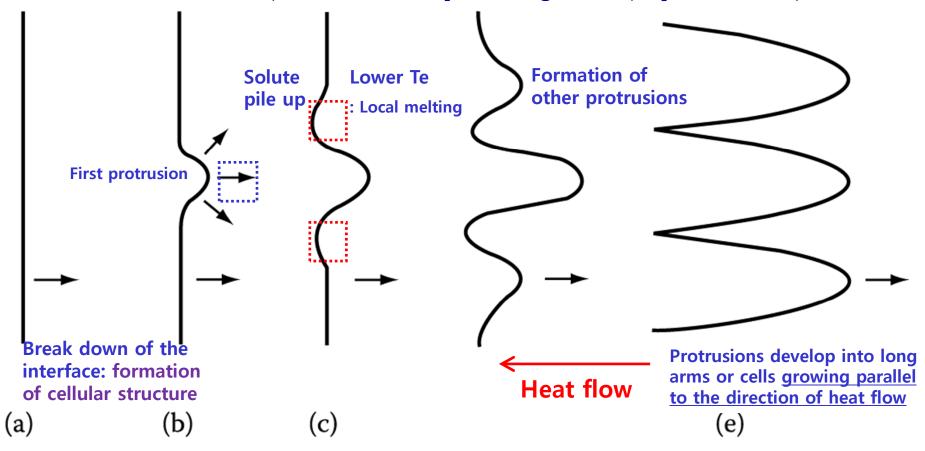


Fig. 4.24 The breakdown of an initially planar solidification front into cells

If temperature gradient ahead of an initially planar interface is gradually reduced below the critical value, (constitutional supercooling at solid/liquid interface)

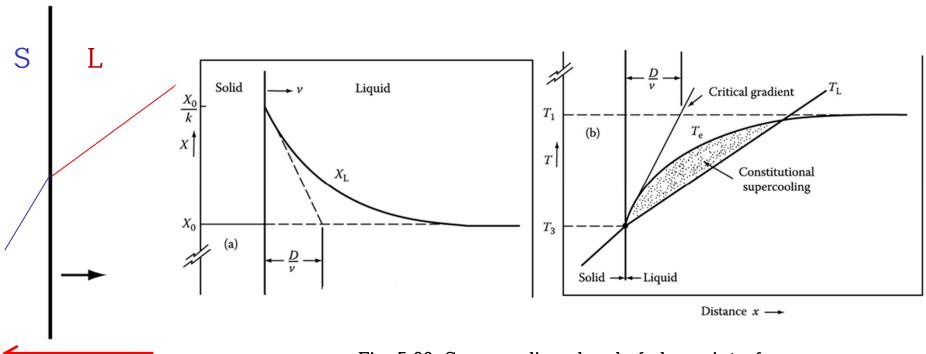
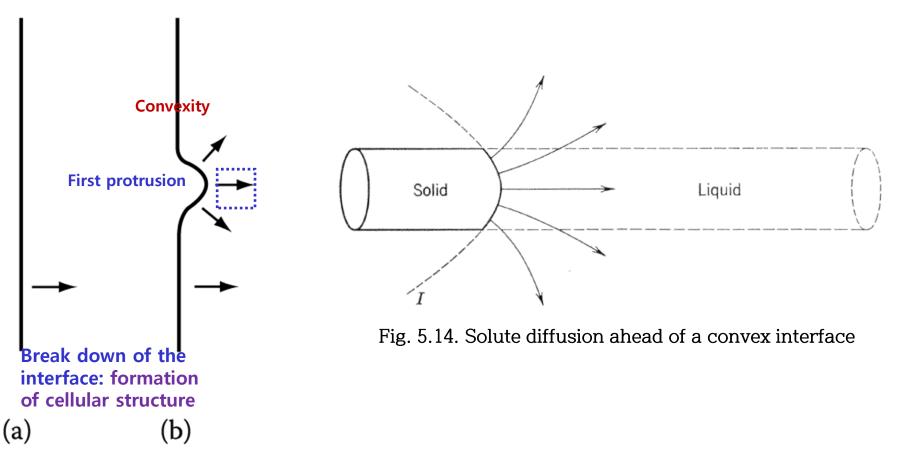


Fig. 5.30. Supercooling ahead of planar interface

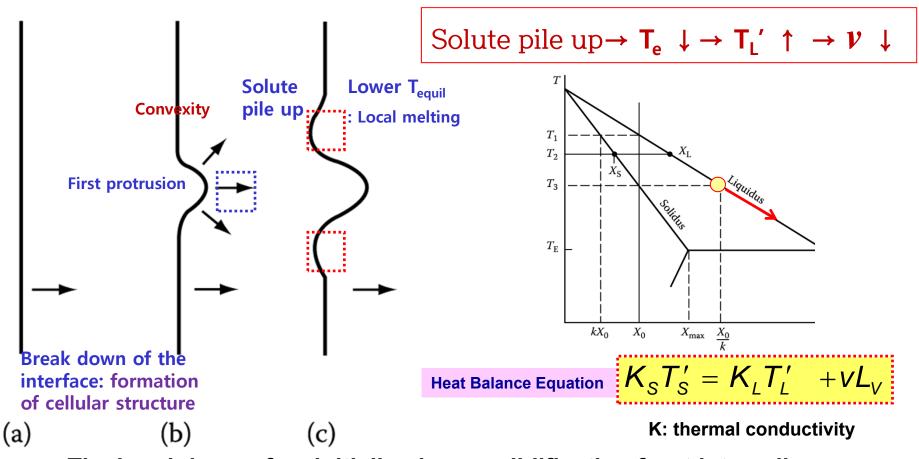
(a)

Heat flow

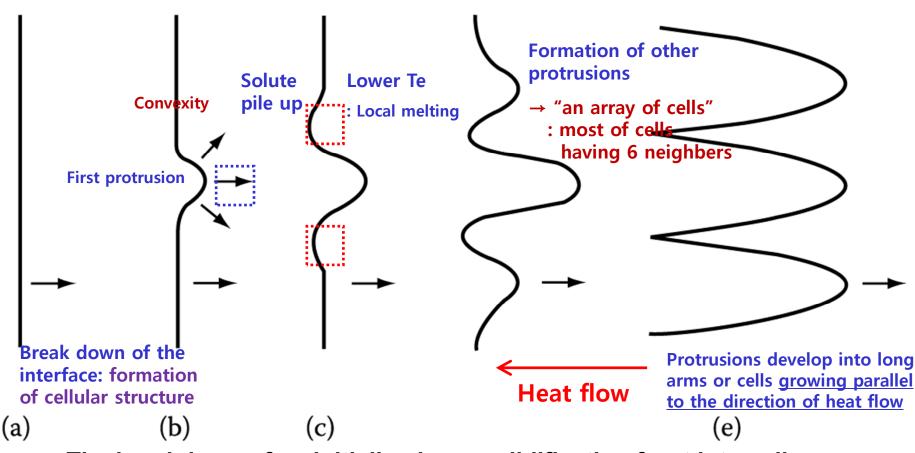
If temperature gradient ahead of an initially planar interface is gradually reduced below the critical value, (constitutional supercooling at solid/liquid interface)



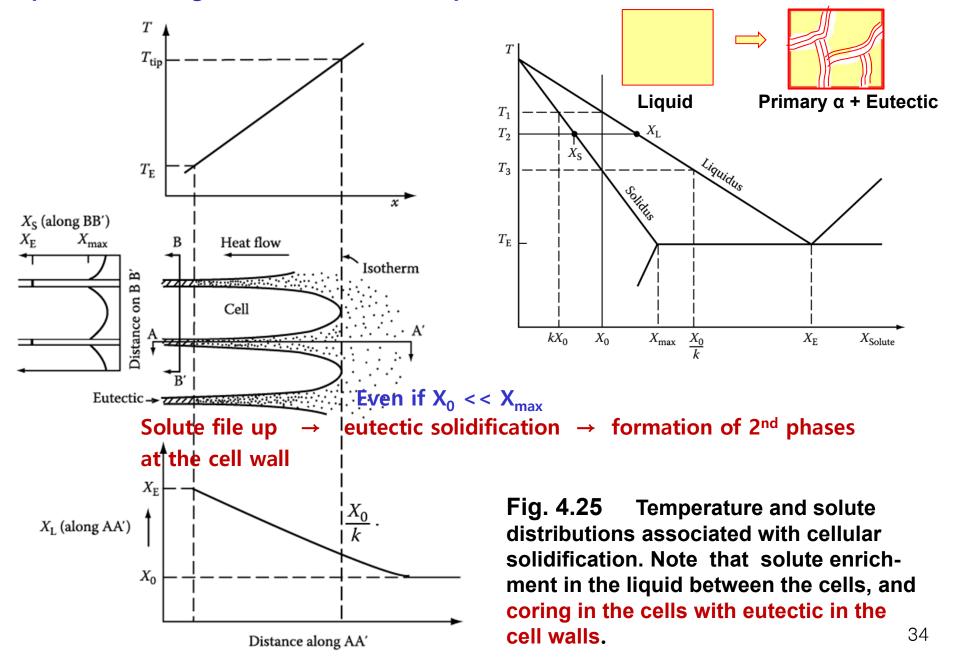
If temperature gradient ahead of an initially planar interface is gradually reduced below the critical value, (constitutional supercooling at solid/liquid interface)

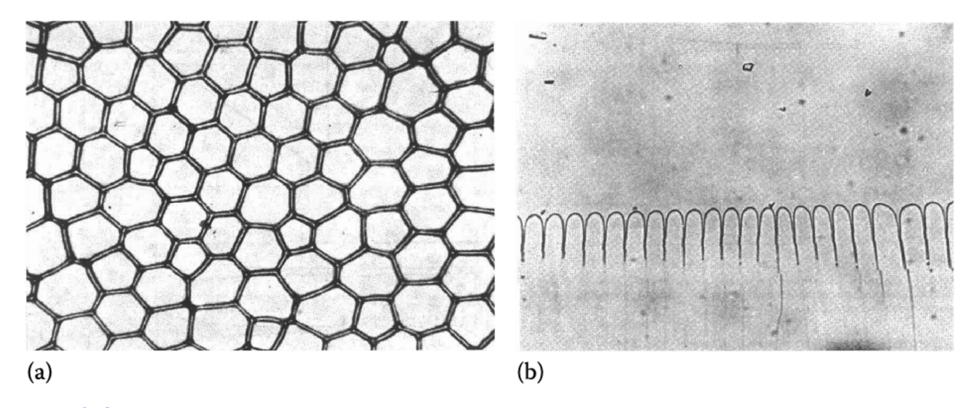


If temperature gradient ahead of an initially planar interface is gradually reduced below the critical value, (constitutional supercooling at solid/liquid interface)



Tips of the cells grow into the hottest liquid and therefore contain the least solute.





* Cellular microstructures

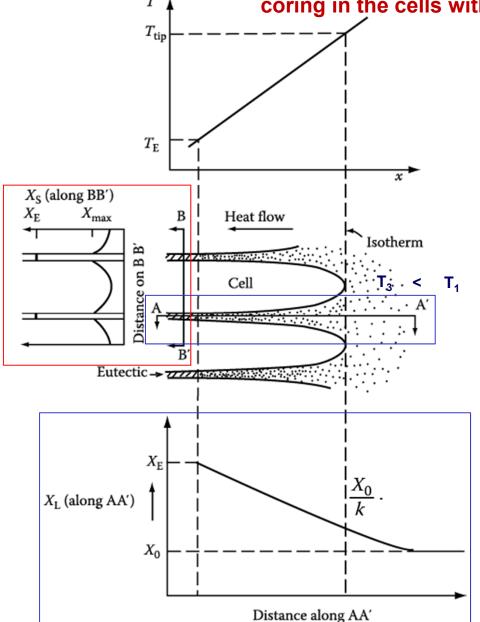
Note that each cell has virtually the same orientation as its neighbors and together they form a single grain.

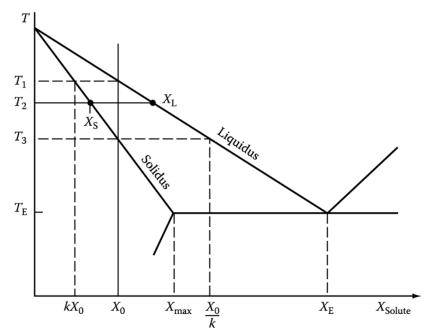
- (a) A decanted interface of a cellularly solidified Pb-Sn alloy (x 120) (after J.W. Rutter in Liquid Metals and Solidification, American Society for Metals, 1958, p. 243).
- (b) Longitudinal view of cells in carbon tetrabromide (x 100) (after K.A. Jackson and J.D. Hunt, Acta Metallurgica 13 (1965) 1212).

Temp. and solute distributions associated with cellular solidification.

1) Note that solute enrichment in the liquid between the cells, and

coring in the cells with eutectic in the cell walls.



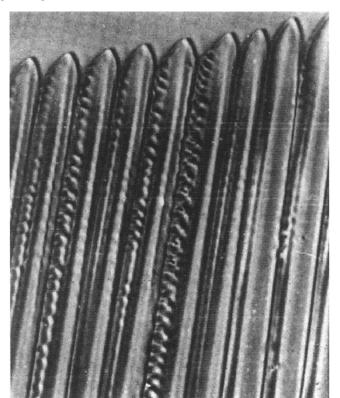


- Tips of the cells grow into the hottest liquid and therefore contain the least solute.
- 3) Even if $X_0 \ll X_{max}$ Solute file up → eutectic solidification → formation of 2nd phases at the cell wall



The change in morphology from cells to dendrites

- * Cellular microstructures are only stable for a certain range of temp. gradients.
- → Sufficiently low temp. gradients → Creation of constitutional supercooling in the liquid between the cells causing interface instabilities in the transverse direction (although, No temp. gradient perpendicular to the growth direction)
- → Develop arms, i.e. dendrites form & Change in the direction of the primary arms away from the direction of heat flow into the crystallographically preferred directions i.e. (100) for cubic metals.





1971, p. 121.)

Fig. 4.27 Cellular dendrites in carbon tetrabromide.

(After L.R. Morris and W.C. Winegard, Journal of Crystal Growth 6 (1969) 61.)

Fig. 4.28 Columnar dendrites in a transparent organic alloy. (After K.A. Jackson in Solidification, American Society for Metals,

Cellular and Dendritic Solidification

At the interface, $T_L = T_e$ (not T_E) = $T_3 \rightarrow T_{L, liquid} = T_1 : T' = T_1 - T_3$ (superheating)

Criterion for the stable planar interface:

```
T_L' > (T_1 - T_3)/(D/v)
                           : the protrusion melts back_steeper than the critical gradient
                          (T<sub>1</sub>-T<sub>3</sub>: Equilibrium freezing range of alloy)
T_1'/v > (T_1-T_3)/D
```

- \longrightarrow Large solidification range of T_1 - T_3 or high ν promotes protrusions.
- need to well-controlled experimental conditions (temp. gradient & growth rate)
- Constitutional supercooling: T₁ ' /v < (T₁-T₃)/D
- Formation of Cell and Dendrites Structures

Solute effect: addition of a very small fraction of a percent solute with very small k ($k = \frac{X_s}{X_s}$) \rightarrow (T₁-T₃) \uparrow promotes dendrites.

Cooling rate effect: Higher cooling rate allow less time for lateral diffusion of the rejected solute and therefore require smaller cell or dendrite arm spacings to avoid constitutional supercooling. 38

Solidification of Pure Metal

: Thermal gradient dominant



Solidification of single phase alloy: Solute redistribution dominant

a) Constitutional supercooling

Planar → Cellular growth → cellular dendritic growth → Free dendritic growth

응고계면에 조성적 과냉의 thin zone 형성에 의함 Dome 형태 선단 / 주변에 hexagonal array

T → 조성적 과냉영역 증가 Cell 선단의 피라미드형상/ 가지 들의 square array/ Dendrite 성장방향쪽으로 성장방향 변화 성장하는 crystal로 부터 발생한 <u>작</u> <u>열을 과냉각 액상쪽으로 방출</u>함에 의해 형성 Dendrite 성장 방향/ Branched rod-type dendrite

→ "Nucleation of new crystal in liquid"

성장이 일어나는 interface 보다 높은 온도

b) Segregation

: normal segregation, grain boundary segregation, cellular segregation, dendritic segregation, inversegregation, coring and intercrystalline segregation, gravity segregation